Processing, Materials, and Integration of Damascene and 3D Interconnects

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Preface

The papers included in this issue of *ECS Transactions* were originally presented in the symposium “Processing, Materials and Integration of Damascene and 3D Interconnects”, held during the 216th meeting of The Electrochemical Society, in Vienna, Austria from October 4 to 9, 2009.

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Facts about ECS

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Processing is a flexible software sketchbook and a language for learning how to code within the context of the visual arts. Since 2001, Processing has promoted software literacy within the visual arts and visual literacy within technology.Â Before we begin drawing in 3D, it's important to note that as soon as we give ourselves over to the illusion of 3D space, a certain amount of control must be relinquished to the P3D renderer. Flake JC, Roozeboom F, Ramm P, Mathad GS, Rathore HS, Leonte OM. Preface: Processing, Materials, and Integration of Damascene and 3D Interconnects . ECS Transactions. 2010 Dec 1;25(38).